

Delocalization of Flux Lines from Extended Defects by Bulk Randomness

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We study the delocalization by bulk randomness of a single flux line (FL) from an extended defect, such as a columnar pin or twin plane. In three dimensions, the FL is always bound to a planar defect, while there is an unpinning transition from a columnar pin. Transfer matrix simulations confirm this picture, and indicate that the divergence of the localization length from the columnar defect is governed by a liberation exponent $\nu = 1.3 \pm 0.6$, for which a "mean-field" estimate gives $\nu = 0.78$. The results, and their extensions, are compared to other theories. The effects may be observable in thin samples close to H_{c1} .

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It is now well known that fluctuations can drastically change the nature of the Abrikosov phase of type II superconductors. Thermal disorder can melt the vortex lattice, forming a vortex liquid at both low and high vortex densities [1]. Quenched randomness also leads to new behavior [2], which depends upon its degree of correlation. Point defects, such as vacancies or interstitials, encourage line wandering, and may lead to the formation of a glassy phase with a non-zero critical current, called a vortex glass [3]. In the extreme low density limit of a single vortex line (FL), analytical [4] and numerical [5] work has shown that this is indeed the case, though the existence of the vortex glass away from H_{c1} is still unclear. More recently, the experimental creation of "columnar," or linear, pinning sites [6] has inspired theoretical treatment of the resulting "Bose glass" phase [7]. Two planes, planar defects which occur naturally as a type of grain boundary, may lead to a different phase [7].

In this letter, we study the behavior of an individual vortex line in the presence of both point disorder and a single extended defect (e.g. a columnar pin; see Fig. 1). The free energy of a d -dimensional FL of length L interacting with an n -dimensional extended defect is

$$F = \int_0^L dz \left[\frac{1}{2} \left(\frac{dx(z)}{dz} \right)^2 + V_R(x(z); z) \right] \quad (x_\perp(z)) \quad ; \quad (1)$$

where $x(z)$ $2^{<d-1}$ is the displacement of the vortex line, $x_\perp(z)$ $2^{<d-n}$ is the component perpendicular to the defect, \sim is the stiffness, (x_\perp) is a short-range potential concentrated near $x_\perp = 0$, and $V_R(x; z)$ is a random potential representing the point disorder, with

$$\langle V_R(x; z) V_R(x^0; z^0) \rangle = \delta^2(x - x^0) \delta^2(z - z^0) \quad (2)$$

For $n = 1$ or $n = 2$, this model describes pinning by a columnar or a planar defect, respectively.

In $d = 3$, the wanderings of a single vortex line (FL) are controlled by the random potential due to impurities. While in higher dimensions, a line freely fluctuating due to thermal effects is stable to weak randomness [4], in this paper we consider mainly situations where the randomness is strong enough to be relevant. In such cases, the behavior at long length scales is dominated by a zero temperature fixed point [3]. However, even at $T = 0$, there can be a non-trivial transition between vortex lines localized or free from the extended defect [8]. The zero temperature phase transition also governs the singular behavior at finite temperatures. The relevance of disorder, and the dominance of zero temperature fixed points simplifies certain aspects of the calculation. The partition sum over all thermally fluctuating configurations is dominated by the optimal path which minimizes Eq. 1, now regarded as an energy.

The behavior of the FL in the absence of the extended defect, $\epsilon = 0$, is well-understood from extensive

theoretical and numerical work [4,9,5]. The energy per unit length is self-averaging and approaches a constant, $E(L) = L^{-1} \langle E(L) \rangle = E_0$; fluctuations in energy and transverse extension also grow with length (albeit more slowly), and are described by non-trivial power-laws

$$E \sim AL^{\epsilon_1} \quad \text{and} \quad x \sim BL^{\epsilon_2} \quad (3)$$

where for short-range correlated disorder, the exponents ϵ_1 and ϵ_2 depend only on d and obey $\epsilon_1 = 2 - \epsilon_2$ [10]. ϵ_1 is exactly $2/3$ in $d = 2$, approximately 0.61 in $d = 3$, and gradually reduces to $1/2$ in higher dimensions [5].

First, we obtain a lower critical dimension by considering if the delocalized FL is stable to infinitesimal pinning, ϵ . If the FL is confined by the defect, following Nattermann and Lipowsky [11] the localization length, ξ , is estimated by minimizing the FL energy

$$E(L; \xi) = L^{-\epsilon_1} + AL^{-\epsilon_2} \quad E_0 L \quad (4)$$

The first term is the attractive contribution from the defect, while the second term uses Eq. 3 to account for the energy cost of confining the FL into $L^{-\epsilon_1}$ regions of length $L^{-\epsilon_1}$ and width ξ . Whether or not the pinning term is dominant at large distances determines its relevance. A weak potential is irrelevant for $d > d_1$, where d_1 is the lower critical dimension, defined by

$$(d_1 - n) = 1 - \epsilon_2 \quad (5)$$

Using the above estimates of ϵ , $d_1 = 2$ for columnar defects ($n = 1$), while $3 < d_1 < 4$ for planar defects ($n = 2$). A single vortex line in three dimensions is thus always pinned by a planar defect. When weak pinning is relevant, minimizing Eq. 4 yields a localization length that diverges for small ϵ as

$$\xi \sim \epsilon^{-\frac{1}{\epsilon_2}}; \quad \text{where} \quad \frac{1}{\epsilon_2} = \frac{1}{1 - \epsilon_1(d - n)} \quad (6)$$

For the planar defect, $\frac{1}{\epsilon_2} = 3/6$. These results are also obtained by power counting in Eq. 1, taking into account the rescaling of temperature.

For $d > d_1$, there is a transition between a delocalized phase for small ϵ and a localized phase for large ϵ . At such a transition, the localization length diverges as

$$\xi \sim \epsilon^{-\frac{1}{\epsilon_2}}; \quad (7)$$

where $(\epsilon_c) = \epsilon_c$ is the reduced pinning strength. This divergence is accompanied by singular behavior in the energy,

$$(\langle E_s(L; \epsilon) \rangle + E_0 L) = L^{-\epsilon_1} \quad (8)$$

which defines a "heat capacity" exponent ϵ . For the borderline dimension $d_1 = 2$ for $n = 1$, numerical simulations indicate a depinning transition as the defect energy is reduced [8].

To construct a mean field (MF) theory of delocalization, consider a FL very near the transition point on the localized side. Such a line makes large excursions away from the defect, forming "bubbles" of typical size z and $\sim z$ in the longitudinal and transverse directions (see Fig. 1). For large z , the energy of a single bubble relative to a pinned segment is

$$E(z) = (E_0)z - A z^{\frac{1}{d-n}} : \quad (9)$$

The first term is the energy cost (per unit length) of leaving the defect to wander in the bulk; the second term is a typical excess energy gain available (at scale z) due to a favorable arrangement of impurities. Minimizing this energy gives the scaling $z^{\frac{1}{d-n}}$ and $\sim z^{\frac{1}{d-n}}$, with

$$\chi_{MF} = 1 - (1 - \frac{1}{d-n}); \text{ and } \chi_{MF} = \frac{1}{d-n} (1 - \frac{1}{d-n}) : \quad (10)$$

Assuming that the probability of encountering a favorable bubble is independent of its length z , the total number of favorable bubbles is proportional to L/z . The energy of the FL thus scales as

$$E(L) / E_0 L + \frac{L}{z} E(z) = (E_0 + \frac{A}{z}) L : \quad (11)$$

The corresponding heat capacity exponent, $\alpha = 0$, satisfies a modified hyperscaling form, $1 - \alpha = (1 - \frac{1}{d-n}) \chi$, appropriate to a zero temperature fixed point.

We know of no obvious way of determining the upper critical dimension for the validity of the MF argument. In low dimensions, the argument may break down in a number of ways. The energy of a bubble configuration, in which interior returns are not allowed, may be different from Eq. 9. Intersections of the defect and the FL become probable when the sum of their fractal dimensions, $n + 1 = \chi$, is greater than d , yielding a critical dimension d_u , which satisfies

$$(d_u - n) = 1 : \quad (12)$$

For columnar defects, $2 < d_u < 3$, while for planar defects, $3 < d_u < 4$. The above result is certainly a lower bound for the true upper critical dimension, but it is important to realize that for the thermal depinning transition it incorrectly gives $d_u - n = 2$, rather than the exact result of $d_u - n = 4$. Other factors, such as a renormalization of the linear term in Eq. 9 by smaller scale bubbles or correlations between adjacent bubbles, may lead to a higher d_u for the disorder-induced delocalization as well. Taken at face value, the above result implies that the case of a columnar pin in three dimensions falls in the mean-field regime. Application of Eq. 10 then gives $\chi = 0.78$, using the numerical values for χ and χ in $d = 3$ [5].

We now describe two approaches that attempt to go beyond the MF treatment. In the "necklace model" applied by Lipowsky and Fisher (LF) to the borderline case of $n = 1$ and $d = 2$ [13], the FL partition function is decomposed into configurations with all possible sequences

of pinned and unpinned (bubble) segments, and calculated by Laplace transforms. For thermal delocalization, since the partial partition functions of pinned and unpinned segments are known, this can be done exactly. In the presence of randomness, the partition functions are not known exactly, and furthermore are themselves random quantities. LF propose using pre-averaged forms that depend only on the exponents χ and χ . Although it is unclear that such pre-averaging faithfully reproduces the desired quenched quantities, LF's results agreed with both replica [8] and numerical [14] treatments of that case. A straightforward extension of their treatment to general n and d , [15] gives

$$\chi(NL) = \begin{cases} \frac{1}{1 - (d-n)} & \text{for } 0 < (d-n) < 1 \\ \frac{1}{(d-n) - 1} & \text{for } 1 < (d-n) < 2 \\ \frac{1}{1 - \chi} & \text{for } 2 < (d-n) \end{cases} \quad (13)$$

These results are substantially different from ours in both low and high dimensions. In particular, for the columnar pin in $d = 3$, the necklace model gives $\chi(NL) = 2.8$. (Hwa has obtained the results of Eq. 13 from a different approach [18].)

A recent preprint [16] by Kolomeisky and Straley (KS) treats this problem for $n = 1$ by the renormalization group (RG), and concludes

$$\chi(KS) = \begin{cases} \frac{1}{1 - \chi(d-1)} & \text{for } 0 < (d-1) < 1 \\ \frac{1}{(d-1) - 1 + \chi} & \text{for } 1 < (d-1) < 2 \\ \frac{1}{1 - \chi} & \text{for } 2 < (d-1) \end{cases} \quad (14)$$

These results coincide with ours in the first regime, and at high dimensions. However, we remain unconvinced about the identification of the upper critical dimension, and the exponents in the intermediate regime [19]. For the case of the columnar pin in three dimensions, Eq. 14 gives $\chi(KS) = 1.5$.

To differentiate between these theories, we examined the problem numerically for columnar and planar defects in three dimensions by a transfer-matrix method, which locates the optimal path exactly in a strip of finite width. To enhance performance, we chose the z direction along the diagonal of a cubic lattice, with random energies on the bonds. The energies of optimal paths terminating at position x at height z obey the recursion relation

$$E(x; z+1) = \min_{x^0: x^0 \neq x} [E(x^0; z) + (x - x^0)g] \quad (15)$$

where $(x; x^0; z)$ is a random energy for the bond connecting x and x^0 at height z , and $(x - x^0)$ is an appropriate lattice delta function indicating when the FL is on the defect. The above recursive computation is polynomial in the length L , allowing us to examine very long lines ($L = 2.5 \times 10^6$ lattice constants with a transverse width $W = 250$ lattice units). The z -averaged end-point

displacement from the defect settles to a constant value, $\langle x^2 \rangle \sim W^2$. In the localized phase, $\langle W \rangle$ converges to a finite value as $W \rightarrow 1$, while in the delocalized phase, it grows as $\langle W \rangle \sim W$. By examining $\langle W \rangle$ for several pinning energies and widths W , we find clear evidence for a depinning transition from a columnar pin, but none from a planar defect (see Fig. 2), consistent with our prediction for d_1 . Log-log fits to power-law forms yield $\gamma = 2.3 \pm 0.1$ for $n = 2$ and $\gamma = 1.3 \pm 0.6$ for $n = 1$ (see Fig. 3). Distance from the critical region may cause additional systematic errors. The curvature in Fig. 3 suggests that this is indeed the case for the planar defect, which may explain the discrepancy with the result of Eq. 6. Given the result for $n = 1$, it is tempting to rule out Eq. 13. However, we must caution that related numerical simulations [14] in $d = 2$, see an effective exponent of $\gamma = 1$ (the mean-field estimate), before reaching the true asymptotic value of $\gamma = 2$. Resolution of this issue requires more extensive simulations.

The actual situation in superconductors is complicated by several factors. Both defects and FLs appear at finite densities and with lengths limited by the sample thickness. First consider a single FL in a random set of columnar pins. The FL can be unpinning from a particular pin by two mechanisms. When the localization length, ξ , becomes comparable to the typical defect separation $\xi_d \sim d^{1/2}$, the FL can freely wander between pins. (It may still be collectively localized by randomness in the distribution of columnar pins at a much larger length scale.) The second mechanism, originally described in the context of the Bose glass [17], involves a long-range hopping mechanism in which a FL wanders to a distant pin. The energy cost of such a move ($\sim L^{1/3}$) is compensated by the fluctuations in pinning energy ($\sim L^{1/2} \sim b$ with $b = 3/(2 - 2)$). A long enough sample, $L \sim L_{\text{hop}} \sim b^{2/3}$, will have sufficiently many favorable regions to allow such hops. The pinning effects described in this paper, are thus applicable only for $L \ll L_{\text{hop}}$ and $\xi \ll \xi_d$. A finite density of FLs introduces another length scale $\xi_{\text{FL}} \sim d^{1/2}$. The dilute Bose glass for $\xi_{\text{FL}} \ll \xi_d$ is subject to the same constraints, and is unstable to the above hopping mechanism [17] for $L \sim L_{\text{hop}}$. In the overdense limit of $\xi_{\text{FL}} \sim \xi_d$, the hopping mechanism is no longer relevant. A remnant of the unpinning transition may still be observed for $\xi_{\text{FL}} \ll \xi_d$. Similar considerations hold for the case of grain boundary pinning.

Columnar pins and grain boundaries are very effective sources of FL pinning in superconductors. However, point defects in the bulk provide a competing mechanism for unpinning FLs from these extended defects. We provide analytical and numerical arguments that the FL is always pinned to a planar defect, but that there is a transition in the case of the columnar pin. The requirements for observation of the transition and the localized phase can be satisfied close to H_{c1} , although the size of this

region in the cuprate materials is extremely narrow. It is hoped that more sensitive probes will be developed to investigate these and other subtle effects in this regime.

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 - [19] It is possible that KS use the perturbative RG equations beyond their range of validity. In particular, they conclude a marginal relevance of ϕ , and hence the absence of a depinning transition in $d = 2$. This is in disagreement with the numerical simulations of [8,14], and the non-perturbative RG of [18].

FIG. 1. A flux line localized around a columnar pin in three dimensions ($d = 3, n = 1$). White portions of the FL indicate when it is on the defect.

FIG. 2. $\langle W \rangle$ for various widths and defect energies for (a) the columnar pin and (b) the planar defect. The bond energies were uniformly distributed integers between 0 and 4095. The region of rapid change near $\epsilon_c \approx 375$ indicates the transition for the columnar pin, while no such feature is present in the case of the planar defect.

FIG. 3. Logarithmic plots of the localization length ξ versus the reduced pinning strength for (a) the columnar pin and (b) the planar defect. The different curves in (a) account for the uncertain value of ϵ_c .